

# PJS6416-AU

## 20V N-Channel Enhancement Mode MOSFET

<b>Voltage</b>	<b>20 V</b>	<b>Current</b>	<b>7.4 A</b>
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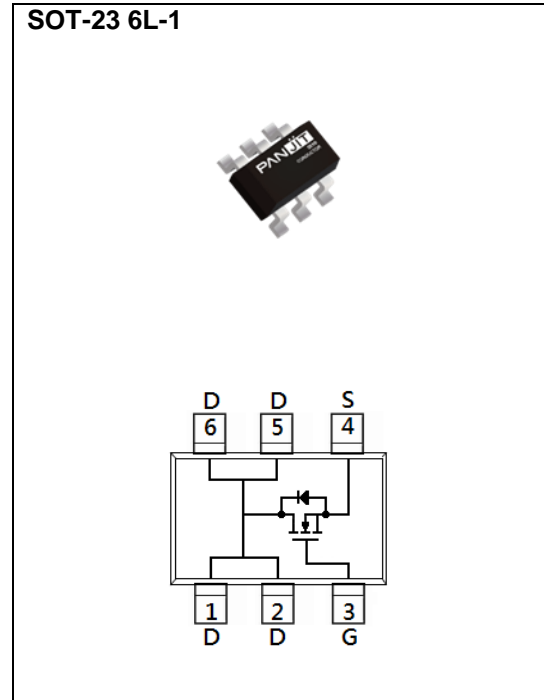
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@7.4A < 24m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@2.5V$ ,  $I_D@4.7A < 34m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@1.8V$ ,  $I_D@1.8A < 74m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc..
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : SOT-23 6L-1 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.014 grams

SOT-23 6L-1



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	$\pm 12$	
Continuous Drain Current <sup>(Note 4)</sup>	$T_A=25^\circ\text{C}$	$I_D$	7.4	A
	$T_A=70^\circ\text{C}$		6	
Pulsed Drain Current	$T_A=25^\circ\text{C}$	$I_{DM}$	29.6	
Power Dissipation <sup>(Note 1)</sup>	$T_a=25^\circ\text{C}$	$P_D$	2	W
	Derate above $25^\circ\text{C}$		16	mW/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^\circ\text{C}$
Thermal Resistance		$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
- Junction to Ambient <sup>(Note 3)</sup>				

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.7	1.2	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =7.4A	-	19	24	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4.7A	-	26	34	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.8A	-	46	74	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =7.4A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	6.7	10	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	2	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	-	513	720	pF
Output Capacitance	C <sub>oss</sub>		-	75	135	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	59	105	
<b>Switching</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =7.4A, V <sub>GS</sub> =4.5V, R <sub>G</sub> =6Ω <sup>(Note 1,2)</sup>	-	6	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	56	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	23	-	
Turn-Off Fall Time	t <sub>f</sub>		-	13	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.77	1.2	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.

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## TYPICAL CHARACTERISTIC CURVES

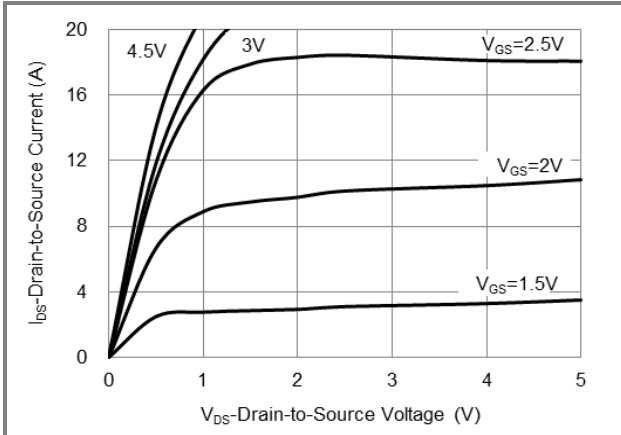


Fig.1 On-Region Characteristics

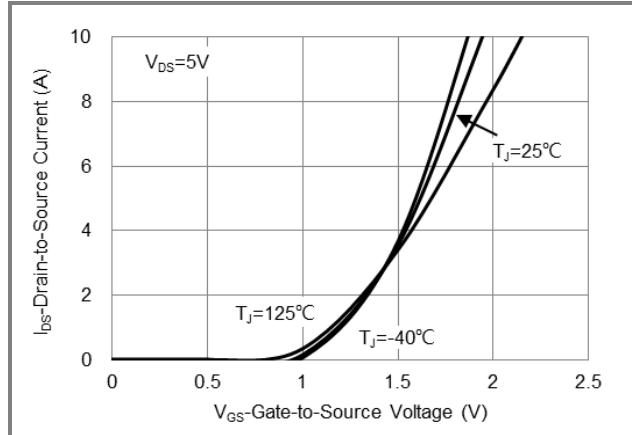


Fig.2 Transfer Characteristics

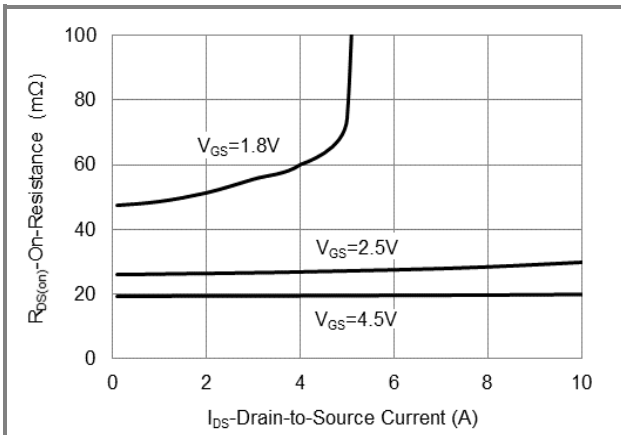


Fig.3 On-Resistance vs. Drain Current

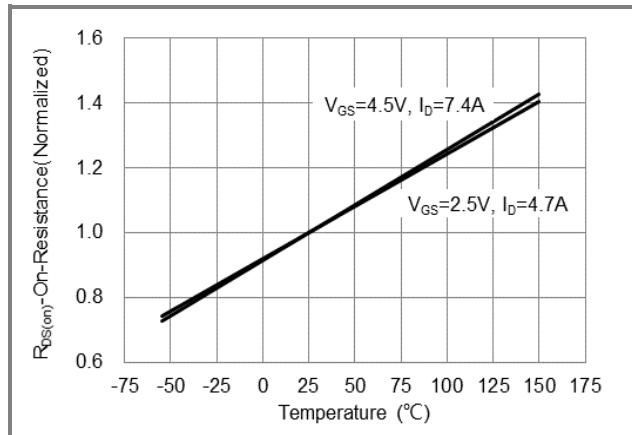


Fig.4 On-Resistance vs. Junction temperature

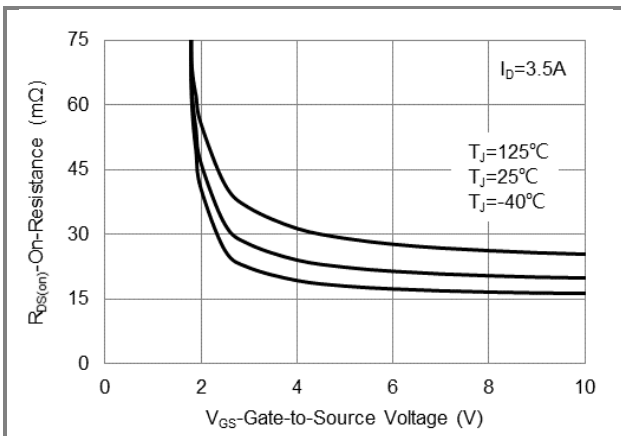


Fig.5 On-Resistance Variation with  $V_{GS}$

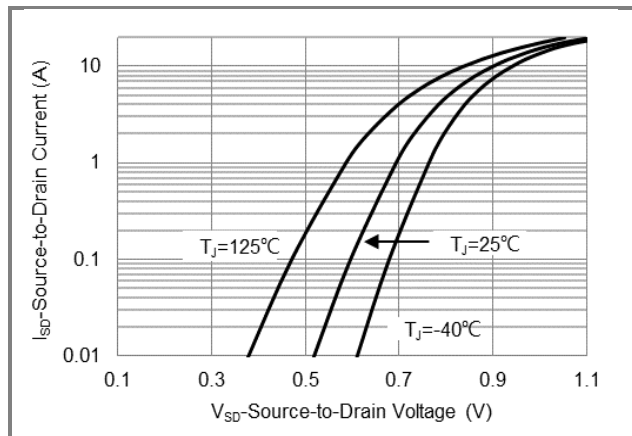


Fig.6 Source-Drain Diode Forward Voltage

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## TYPICAL CHARACTERISTIC CURVES

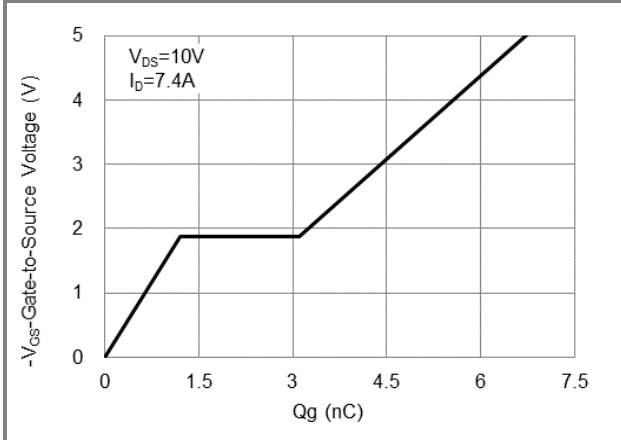


Fig.7 Gate-Charge Characteristics

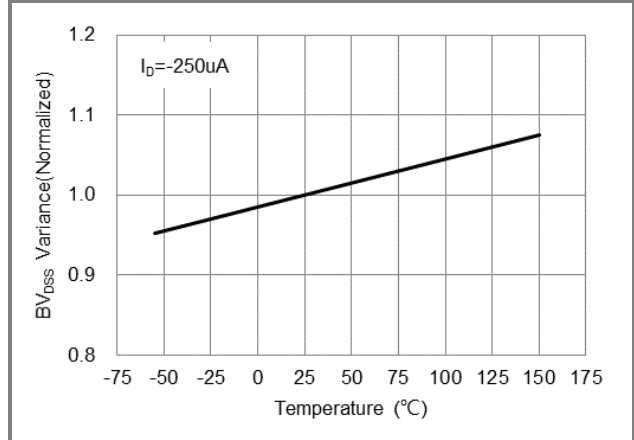


Fig.8 Breakdown Voltage Variation vs. Temperature

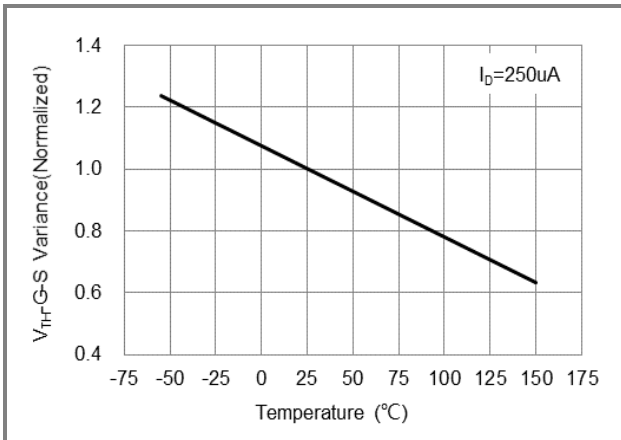


Fig.9 Threshold Voltage Variation with Temperature

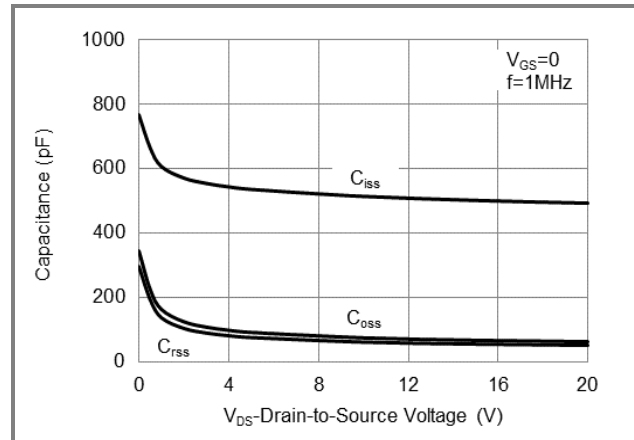


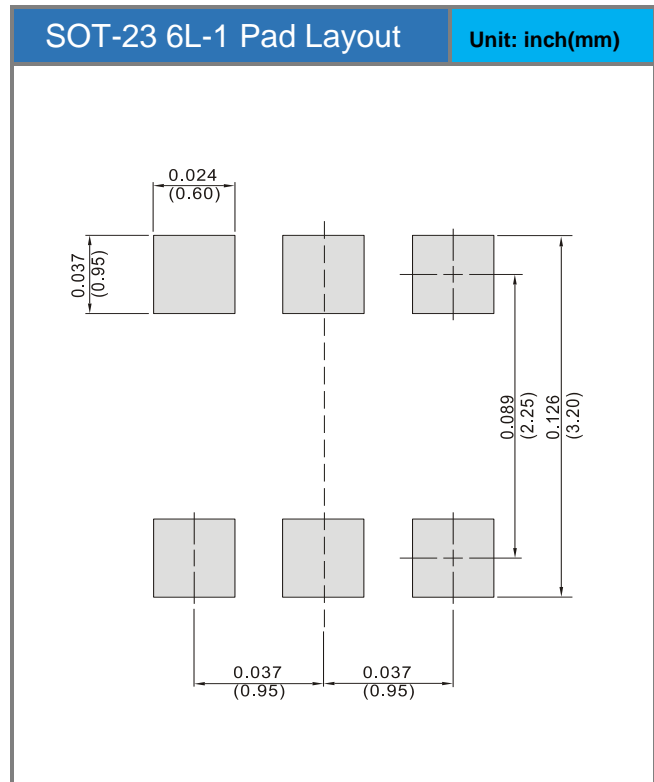
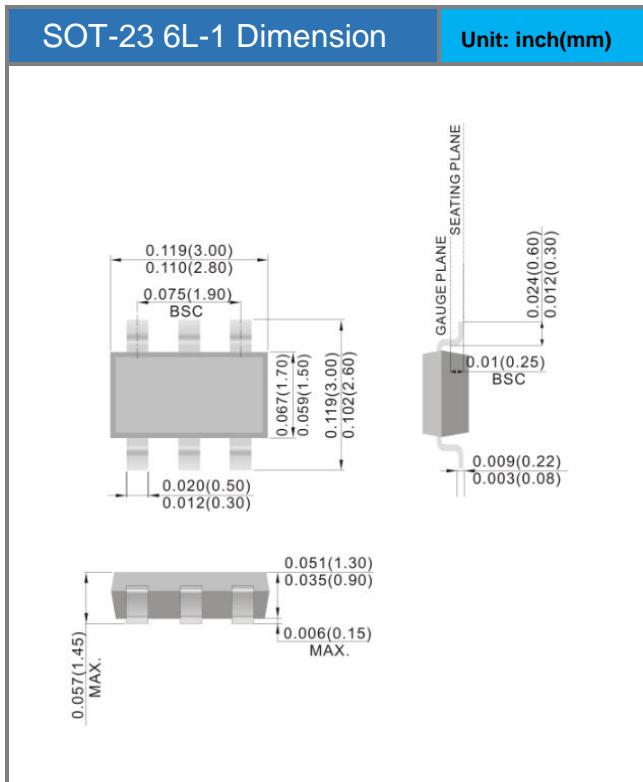
Fig.10 Capacitance vs. Drain-Source Voltage

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## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJS6416-AU	SOT-23 6L-1	3K pcs / 7" reel	S16

## Packaging Information & Mounting Pad Layout



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